

Supporting Information

Impact of Preferential Indium Nucleation on Electrical Conductivity of VLS Grown Indium-Tin-Oxide Nanowires

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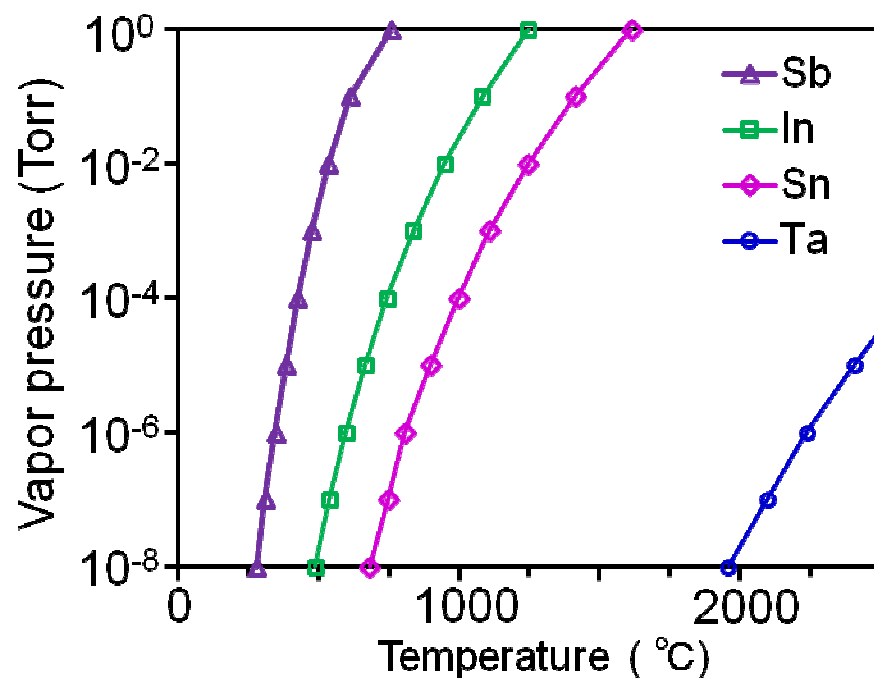


Figure S1. Temperature dependence data of vapor pressures for In, Sn, Sb and Ta.

It can be seen that the difference between indium and tin on the vapor pressures at a given temperature is much smaller than other elements. These data were taken from the reference: Binnewies, M.; Milke, E. Thermochemical data of elements and compounds; Wiley-VCH: Weinheim ; Chichester, 1999.